

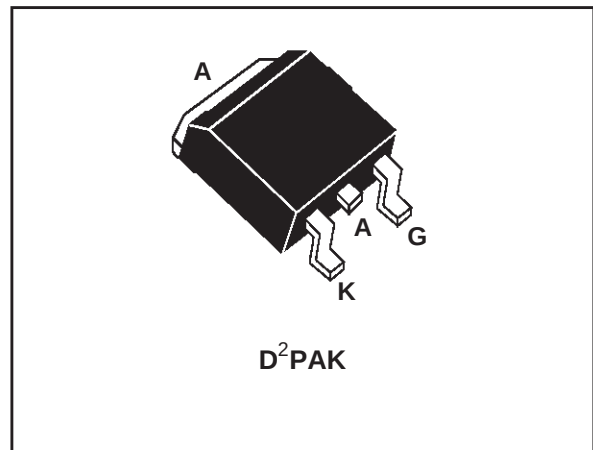
FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY

DESCRIPTION

The TN1625 series of Silicon Controlled Rectifiers uses a high performance glass passivated technology.

This SCR is designed for power supplies up to 400Hz on resistive or inductive load.


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	$T_c = 110^\circ\text{C}$	16	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)	$T_c = 110^\circ\text{C}$	10	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 8.3 \text{ ms}$	199	A
		$t_p = 10 \text{ ms}$	190	
I^2t	I^2t Value for fusing	$t_p = 10 \text{ ms}$	180	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 100 \text{ mA}$ $di_G/dt = 1 \text{ A}/\mu\text{s}$.		100	$\text{A}/\mu\text{s}$
T_{stg} T_j	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125	$^\circ\text{C}$
TI	Maximum temperature for soldering during 10 s		260	$^\circ\text{C}$

Symbol	Parameter	TN1625-		Unit
		600G	800G	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$	600	800	V

TN1625-G

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient (S=1cm ²)	45	°C/W
Rth(j-c)	Junction to case for D.C	1.1	°C/W

GATE CHARACTERISTICS

P_G (AV)= 1W P_{GM} = 10 W (tp = 20 μ s) I_{GM} = 4 A (tp = 20 μ s) V_{RGM} = 5V

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Type	Value	Unit
I_{GT}	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	MIN	3	mA
			MAX	25	
V_{GT}	$V_D = 12V$ (DC) $R_L = 33\Omega$	$T_j = 25^\circ C$	MAX	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3k\Omega$	$T_j = 125^\circ C$	MIN	0.2	V
I_H	$I_T = 100mA$ Gate open	$T_j = 25^\circ C$	MAX	40	mA
I_L	$I_G = 1.2 I_{GT}$	$T_j = 25^\circ C$	MAX	60	mA
V_{TM}	$I_{TM} = 32A$ tp = 380 μ s	$T_j = 25^\circ C$	MAX	1.5	V
I_{DRM}	$V_D = V_{DRM}$	$T_j = 25^\circ C$	MAX	5	μA
I_{RRM}	$V_R = V_{RRM}$	$T_j = 125^\circ C$	MAX	2	mA
dV/dt	$V_D = 67\% V_{DRM}$ Gate open	$T_j = 125^\circ C$	MIN	500	V/ μ s

ORDERING INFORMATION Add "-TR" suffix for Tape & Reel shipment

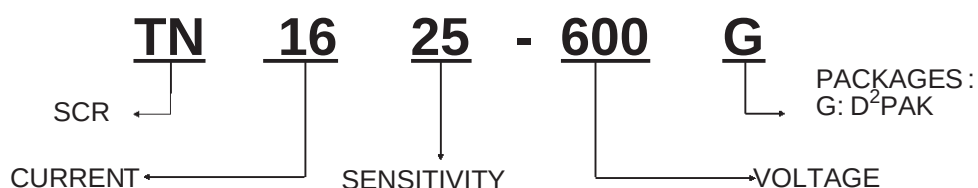


Fig. 1: Maximum average power dissipation versus average on-state current .

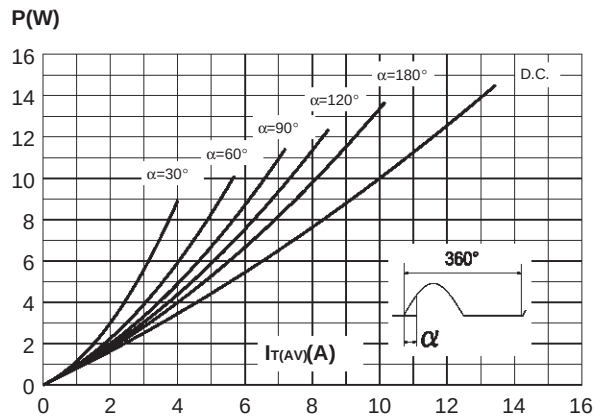


Fig. 3: Average and D.C. on-state current versus case temperature.

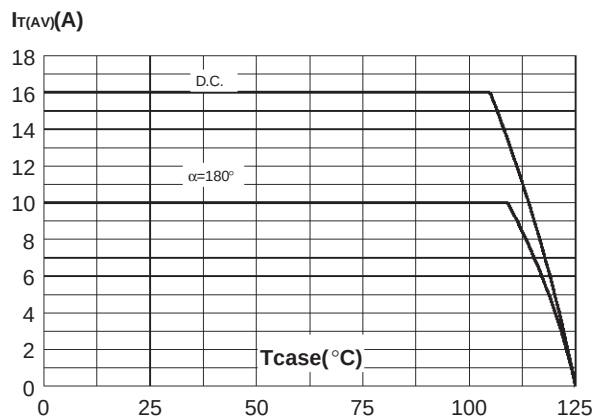


Fig. 5: Relative variation of gate trigger current and holding current versus junction temperature.

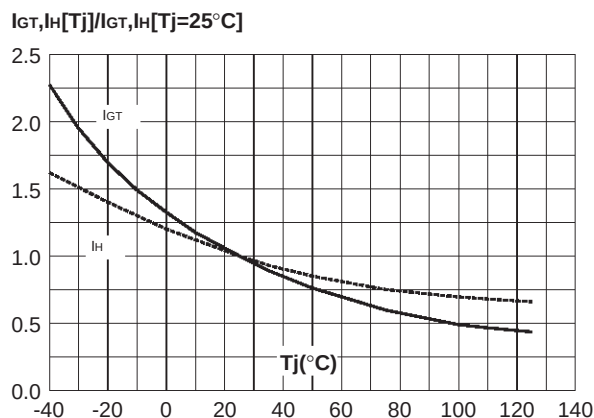


Fig. 2 : Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink+contact.

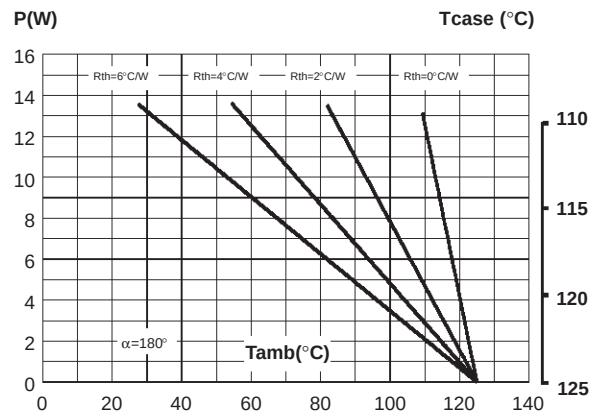


Fig. 4: Relative variation of thermal impedance versus pulse duration.

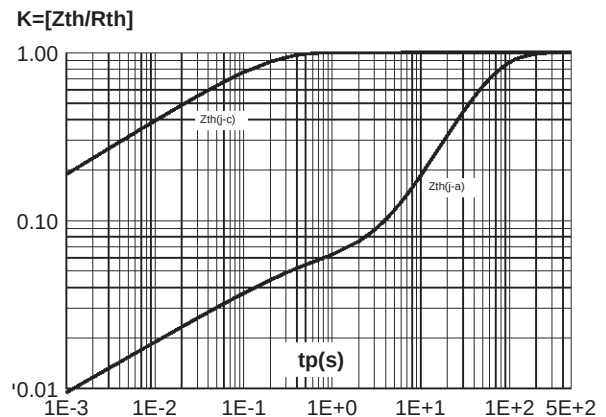


Fig. 6: Non repetitive surge peak on-state current versus number of cycles.

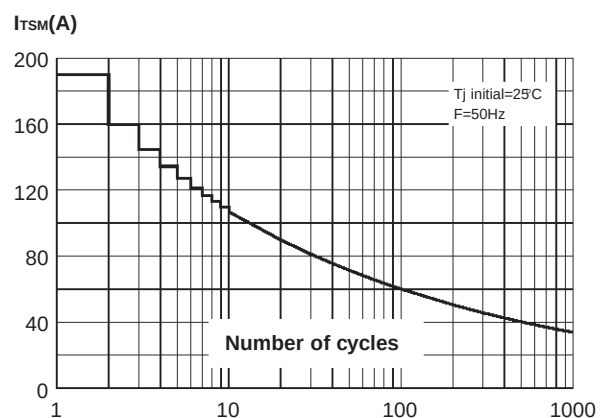


Fig. 7: Non repetitive surge peak on-state current for a sinusoidal pulse, with width $t_p < 10\text{ms}$, and corresponding value of I_t^2 .

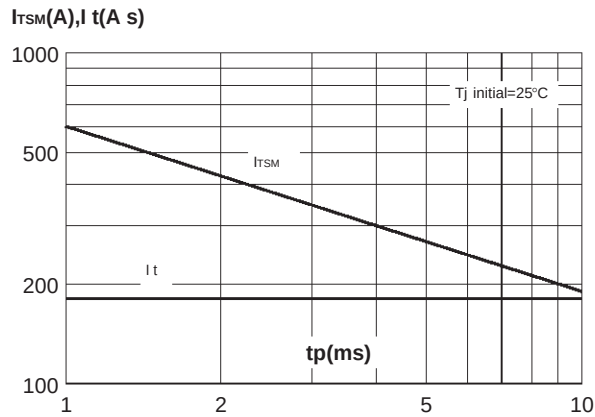


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm).

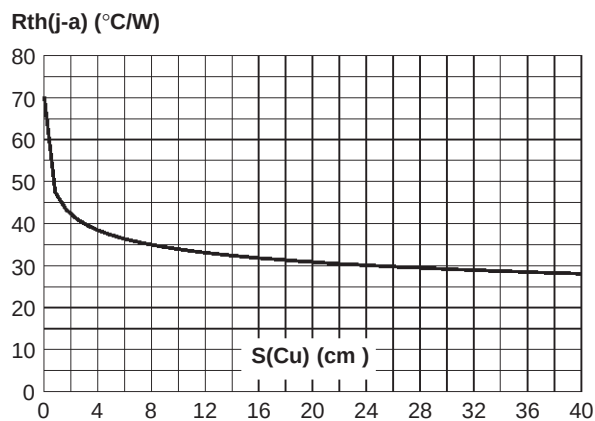


Fig. 8: On-state characteristics (maximum values).

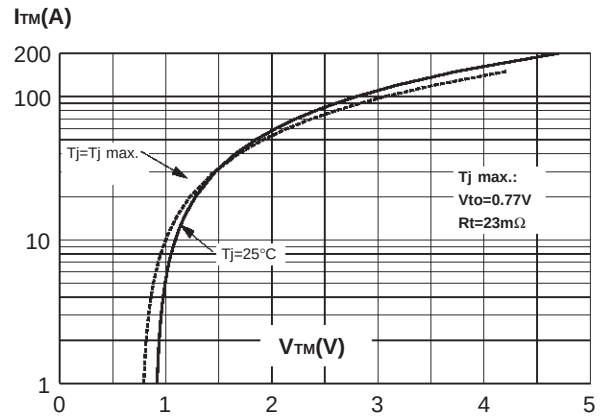
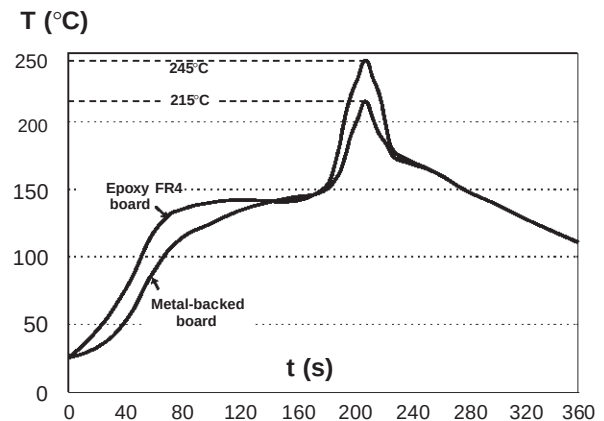
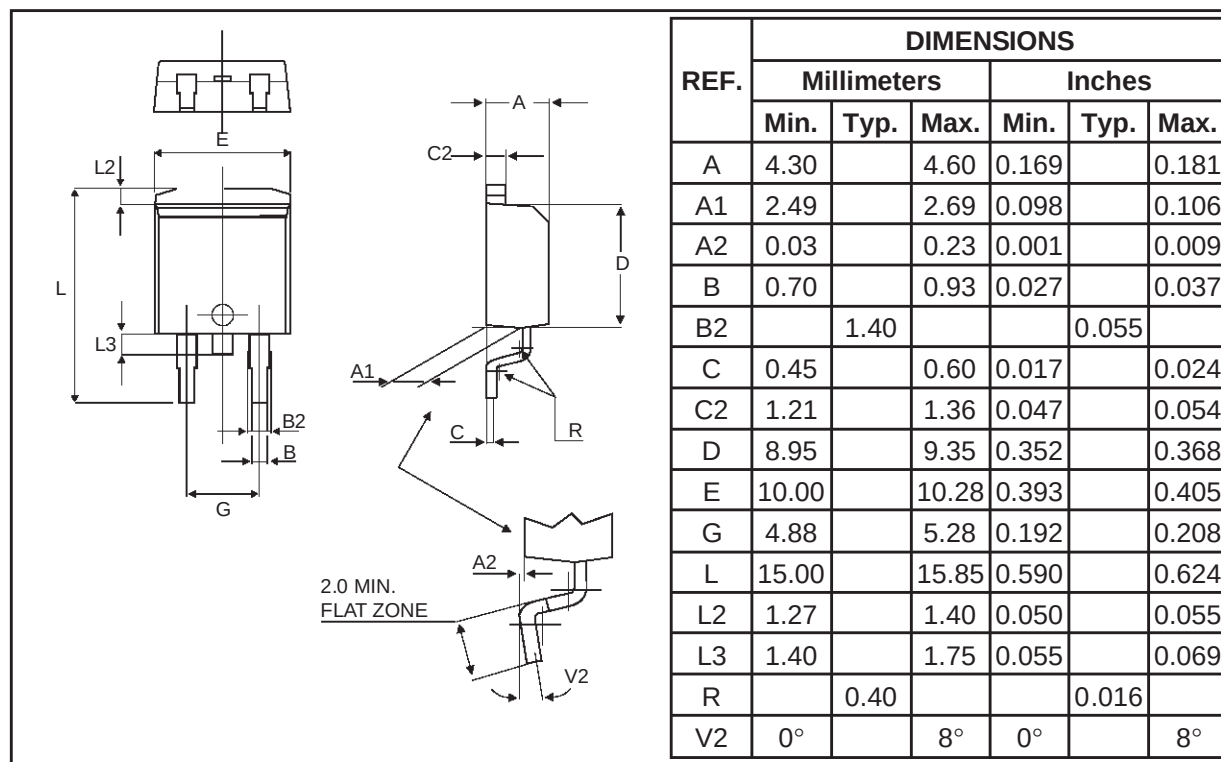


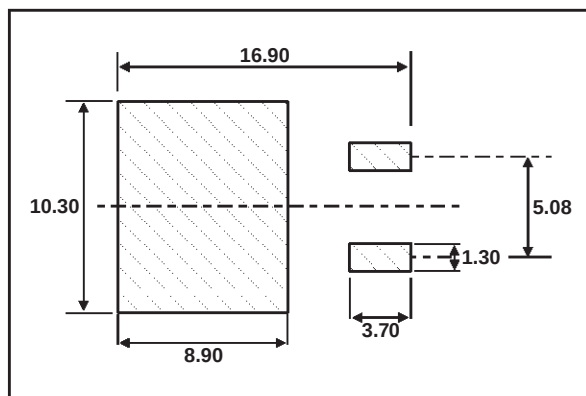
Fig. 10: Typical reflow soldering heat profile, either for mounting on FR4 or metal-backed boards.



PACKAGE MECHANICAL DATA

D²PAK

FOOT PRINT DIMENSIONS (in millimeters)



MARKING: TN1625
x00G

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